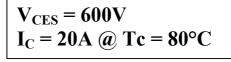
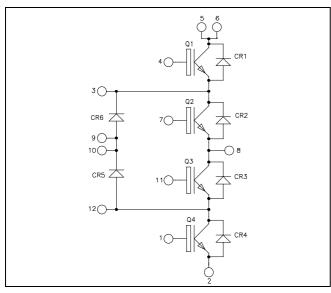
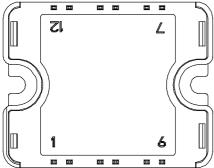


# Three level inverter Trench + Field Stop IGBT3 Power Module







All multiple inputs and outputs must be shorted together 5/6; 9/10

#### Application

- Solar converter
- Uninterruptible Power Supplies

#### **Features**

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- High level of integration

#### **Benefits**

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

#### O1 to O4 Absolute maximum ratings

| Q1 10 Q   | 1 1 10 5 0 1 d t t t t t t t t t t t t t t t t t t |                                  |             |      |
|-----------|--|----------------------------------|-------------|------|
| Symbol    | Parameter  |                                  | Max ratings | Unit |
| $V_{CES}$ | Collector - Emitter Breakdown Voltage              |                                  | 600         | V    |
| т         | Continuous Collector Current                       | $T_C = 25^{\circ}C$              | 32          |      |
| $I_{C}$   | Continuous Conector Current                        | $T_C = 80^{\circ}C$              | 20          | A    |
| $I_{CM}$  | Pulsed Collector Current                           | $T_C = 25^{\circ}C$              | 40          |      |
| $V_{GE}$  | Gate – Emitter Voltage                             |                                  | ±20         | V    |
| $P_{D}$   | Maximum Power Dissipation                          | $T_C = 25^{\circ}C$              | 62          | W    |
| RBSOA     | Reverse Bias Safe Operating Area                   | $T_{\rm J} = 150^{\circ}{\rm C}$ | 40A @ 550V  |      |

These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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#### All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

#### **Q1 to Q4 Electrical Characteristics**

| Symbol        | Characteristic                       | Test Conditions                    |                | Min | Typ | Max | Unit |
|---------------|--------------------------------------|------------------------------------|----------------|-----|-----|-----|------|
| $I_{CES}$     | Zero Gate Voltage Collector Current  | $V_{GE} = 0V, V_{CE} = 600V$       |                |     |     | 250 | μΑ   |
| V             | Collector Emitter Saturation Voltage | $V_{GE} = 15V$                     | $T_j = 25$ °C  |     | 1.5 | 1.9 | V    |
| $V_{CE(sat)}$ |                                      | $I_C = 20A$ $T_j =$                | $T_j = 150$ °C |     | 1.7 |     | V    |
| $V_{GE(th)}$  | Gate Threshold Voltage               | $V_{GE} = V_{CE}, I_C = 300 \mu A$ |                | 5.0 | 5.8 | 6.5 | V    |
| $I_{GES}$     | Gate – Emitter Leakage Current       | $V_{GE} = 20V, V_{CE} = 0V$        |                |     |     | 300 | nA   |

#### Q1 to Q4 Dynamic Characteristics

| Symbol              | Characteristic                      | Test Conditions  |                                       | Min | Typ  | Max  | Unit |
|---------------------|-------------------------------------|--|---------------------------------------|-----|------|------|------|
| $C_{ies}$           | Input Capacitance                   | $V_{GE} = 0V$  |                                       |     | 1100 |      |      |
| Coes                | Output Capacitance                  | $V_{CE} = 25V$<br>f = 1MHz   |                                       |     | 70   |      | pF   |
| C <sub>res</sub>    | Reverse Transfer Capacitance        |  |                                       |     | 35   |      |      |
| $Q_{G}$             | Gate charge                         | $V_{GE}=\pm 15V, I_{C}=2V_{CE}=300V$   |                                       | 0.2 |      | μС   |      |
| $T_{d(on)}$         | Turn-on Delay Time                  | Inductive Switch   |                                       | 110 |      |      |      |
| $T_{r}$             | Rise Time                           | $V_{GE} = \pm 15V$   |                                       |     | 45   |      |      |
| $T_{d(off)}$        | Turn-off Delay Time                 | $V_{\text{Bus}} = 300V$ $I_{\text{C}} = 20A$   |                                       |     | 200  |      | ns   |
| $T_{\mathrm{f}}$    | Fall Time                           | $R_G = 12\Omega$   |                                       | 40  |      |      |      |
| $T_{d(on)}$         | Turn-on Delay Time                  | Inductive Switch   |                                       | 120 |      | ns   |      |
| $T_{\rm r}$         | Rise Time                           | $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_{C} = 20A$ $R_{G} = 12\Omega$   |                                       |     | 50   |      |      |
| T <sub>d(off)</sub> | Turn-off Delay Time                 |  |                                       |     | 250  |      |      |
| $T_{\mathrm{f}}$    | Fall Time                           |  |                                       |     | 60   |      |      |
| Eon                 | Turn-on Switching Energy            | $ \begin{array}{lll} V_{GE} = \pm 15 V & T_{j} = 25^{\circ} C \\ V_{Bus} = 300 V & T_{j} = 150^{\circ} C \\ I_{C} = 20 A & T_{j} = 25^{\circ} C \\ R_{G} = 12 \Omega & T_{j} = 150^{\circ} C \end{array} $ | $T_j = 25^{\circ}C$                   |     | 0.11 |      | mJ   |
| Lon                 |                                     |  |                                       | 0.2 |      | 1113 |      |
| $E_{off}$           | Turn-off Switching Energy           |  |                                       |     | 0.5  |      | mJ   |
| <b>⊥</b> off        | Turn on Switching Energy            |  | $T_j = 12\Omega$ $T_j = 150^{\circ}C$ |     | 0.7  |      | 1113 |
| $I_{sc}$            | Short Circuit data                  | $V_{GE} \le 15V ; V_{Bus} = 360V$<br>$t_p \le 6\mu s ; T_i = 150^{\circ}C$   |                                       |     | 100  |      | A    |
| $R_{thJC}$          | Junction to Case Thermal Resistance |  |                                       |     |      | 2.4  | °C/W |



# CR1 to CR6 diode ratings and characteristics Symbol Characteristic Test Co.

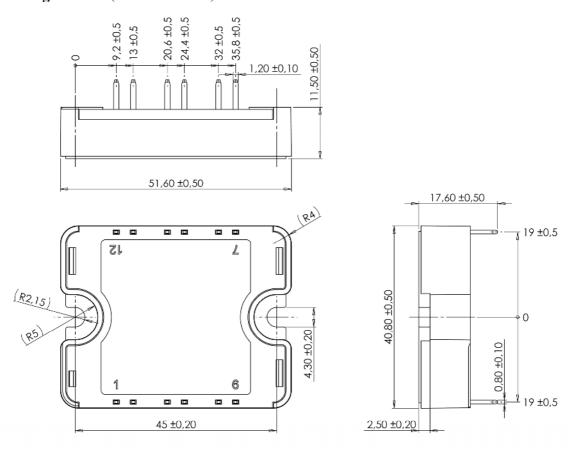
| Symbol                     | Characteristic                             | Test Conditions           |   | Min | Тур  | Max        | Unit |
|----------------------------|--|---------------------------|---|-----|------|------------|------|
| $V_{RRM}$                  | Maximum Peak Repetitive Reverse Voltage    |                           |   | 600 |      |            | V    |
| $I_{RM}$                   | Maximum Reverse Leakage Current            | V <sub>R</sub> =600V      | $T_i = 25^{\circ}C$<br>$T_i = 150^{\circ}C$ |     |      | 150<br>350 | μΑ   |
| $I_{\mathrm{F}}$           | DC Forward Current                         |                           | $Tc = 80^{\circ}C$                          |     | 20   | 330        | A    |
| $V_{\mathrm{F}}$           | Diode Forward Voltage                      | $I_F = 20A$ $V_{GE} = 0V$ | $T_i = 25^{\circ}C$                         |     | 1.6  | 2          | V    |
| <b>v</b> <sub>F</sub>      |  |                           | $T_{i} = 150^{\circ}C$                      |     | 1.5  |            | v    |
| t <sub>rr</sub>            | Reverse Recovery Time                      |                           | $T_j = 25^{\circ}C$                         |     | 100  |            | ns   |
| ۰rr                        |  |                           | $T_{j} = 150^{\circ}C$                      |     | 150  |            | 115  |
| 0                          | $Q_{rr}$ Reverse Recovery Charge $V_R = 3$ | $I_F = 20A$ $V_R = 300V$  | $T_j = 25$ °C                               |     | 1.1  |            | μC   |
| Qrr                        |  | $di/dt = 1600 A/\mu s$    | $T_{i} = 150^{\circ}C$                      |     | 2.3  |            | μС   |
| Е                          | E <sub>rr</sub> Reverse Recovery Energy    |                           | $T_j = 25$ °C                               |     | 0.23 |            | mJ   |
| $\mathbf{E}_{\mathrm{rr}}$ |  |                           | $T_{\rm j} = 150^{\circ}{\rm C}$            |     | 0.50 |            | 1113 |
| $R_{thJC}$                 | Junction to Case Thermal Resistance        |                           |   |     |      | 3.25       | °C/W |

#### Thermal and package characteristics

| Symbol      | Characteristic   |             |    | Min  | Тур | Max | Unit |
|-------------|--|-------------|----|------|-----|-----|------|
| $V_{ISOL}$  | RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz |             |    | 4000 |     |     | V    |
| $T_{J}$     | Operating junction temperature range                           |             |    | -40  |     | 175 | °C   |
| $T_{STG}$   | Storage Temperature Range                                      |             |    | -40  |     | 125 |      |
| $T_{\rm C}$ | Operating Case Temperature                                     |             |    | -40  |     | 100 |      |
| Torque      | Mounting torque  | To heatsink | M4 | 2    |     | 3   | N.m  |
| Wt          | Package Weight   |             |    |      |     | 110 | g    |



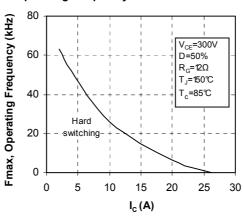
#### SP1 Package outline (dimensions in mm)



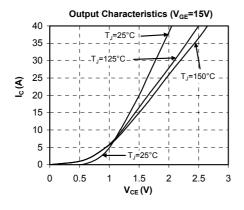
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

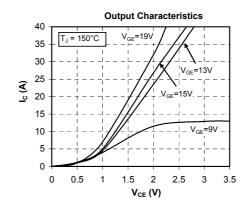
#### Q1 to Q4 Typical performance curve

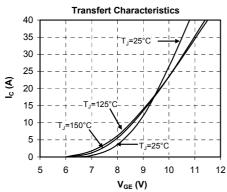
#### **Operating Frequency vs Collector Current**

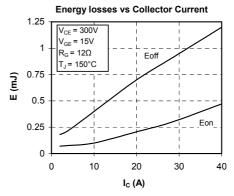


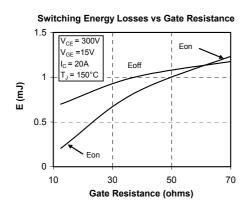


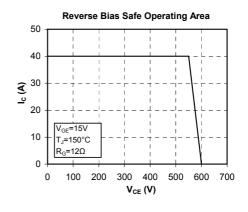


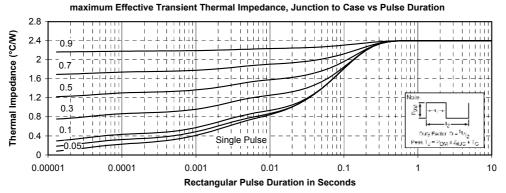








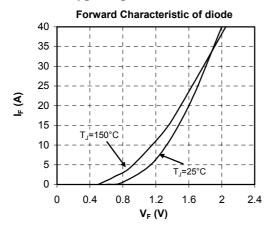




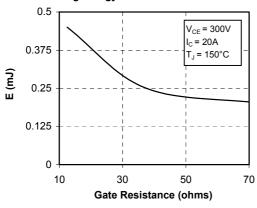
5 - 7



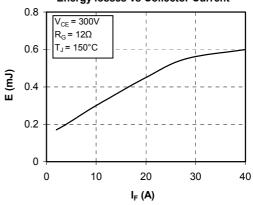
#### CR1 to CR6 Typical performance curve



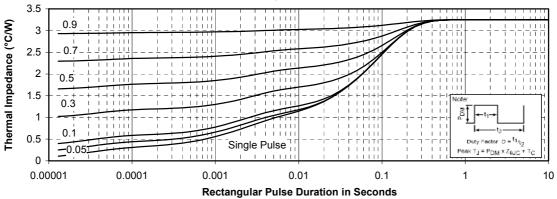
#### Switching Energy Losses vs Gate Resistance



#### **Energy losses vs Collector Current**



#### maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration





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